DATA SHEET

BUJ105AB
Silicon Diffused Power Transistor

Product specification

October 2018

WeEn
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Silicon Diffused Power Transistor BUJ105AB

GENERAL DESCRIPTION

High-voltage, high-speed planar-passivated npn power switching transistor in SOT404 (D^2-PAK) surface-mount package intended for use in high frequency electronic lighting ballast applications, converters, inverters, switching regulators, motor control systems, etc.

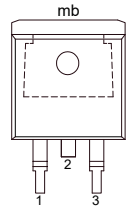
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	V_{BE} = 0 V	-	700	V
V_{CBO}	Collector-Base voltage (open emitter)		-	700	V
V_{CEO}	Collector-emitter voltage (open base)		-	400	V
I_C	Collector current (DC)		-	8	A
I_{CM}	Collector current peak value		-	16	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25$ ˚C	-	125	W
V_{CEsat}	Collector-emitter saturation voltage	I_C = 4.0 A;I_B = 0.8 A	0.3	1.0	V
h_{FEsat}		I_C = 4.0 A; V_{CE} = 5 V	11	15	
t_f	Fall time	I_C = 5 A; I_{B1} = 1 A	20	50	ns

PINNING - SOT404

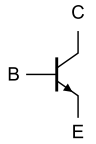
PIN	DESCRIPTION
1	base
2	collector
3	emitter
mb	collector

PIN CONFIGURATION



D2PAK (SOT404)

SYMBOL



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LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	Collector to emitter voltage	V_{BE} = 0 V	-	700	V
V_{CEO}	Collector to emitter voltage (open base)		-	400	V
V_{CBO}	Collector to base voltage (open emitter)		-	700	V
I_C	Collector current (DC)		-	8	A
I_{CM}	Collector current peak value		-	16	A
I_B	Base current (DC)		-	4	A
I_{BM}	Base current peak value		-	8	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25$ ˚C	-	125	W
T_{stg}	Storage temperature		-65	150	˚C
T_j	Junction temperature		-	150	˚C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Thermal resistance junction to mounting base		-	1.0	K/W
$R_{th\ j\text{-}a}$	Thermal resistance junction to ambient	minimum footprint, FR4 board	55	-	K/W

STATIC CHARACTERISTICS

T_{mb} = 25 ˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CES},I_{CBO}	Collector cut-off current [1]	V_{BE} = 0 V; V_{CE} = $V_{CESMmax}$	-	-	0.2	mA
I_{CES}		V_{BE} = 0 V; V_{CE} = $V_{CESMmax}$; T_j = 125 ˚C	-	-	0.5	mA
I_{CEO}	Collector cut-off current	V_{CEO} = $V_{CEOMmax}$ (400V)	-	-	0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB} = 9 V; I_C = 0 A	-	-	1	mA
$V_{CEOsust}$	Collector-emitter sustaining voltage	I_B = 0 A; I_C = 10 mA; L = 25 mH	400	-	-	V
V_{CEsat}	Collector-emitter saturation voltage	I_C = 4.0 A;I_B = 0.8 A	-	0.3	1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C = 4.0 A;I_B = 0.8 A	-	1.0	1.5	V
h_{FE}	DC current gain	I_C = 1 mA; V_{CE} = 5 V	10	14	34	
h_{FE}		I_C = 500 mA; V_{CE} = 5 V	13	23	36	
h_{FEsat}		I_C = 4.0 A; V_{CE} = 5 V	8	11	15	

DYNAMIC CHARACTERISTICS

T_{mb} = 25 ˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
	Switching times (resistive load)	I_{Con} = 5 A; I_{Bon} = -I_{Boff} = 1 A; R_L = 75 ohms; V_{BB2} = 4 V;			
t_{on}	Turn-on time		0.65	1	µs
t_s	Turn-off storage time		1.8	2.5	µs
t_f	Turn-off fall time		0.3	0.5	µs
	Switching times (inductive load)	I_{Con} = 5 A; I_{Bon} = 1 A; L_B = 1 µH; -V_{BB} = 5 V			
t_s	Turn-off storage time		1.2	1.7	µs
t_f	Turn-off fall time		20	50	ns
	Switching times (inductive load)	I_{Con} = 5 A; I_{Bon} = 1 A; L_B = 1 µH; -V_{BB} = 5 V; T_j = 100 ˚C			
t_s	Turn-off storage time		1.4	1.9	µs
t_f	Turn-off fall time		25	100	ns

1 Measured with half sine-wave voltage (curve tracer).

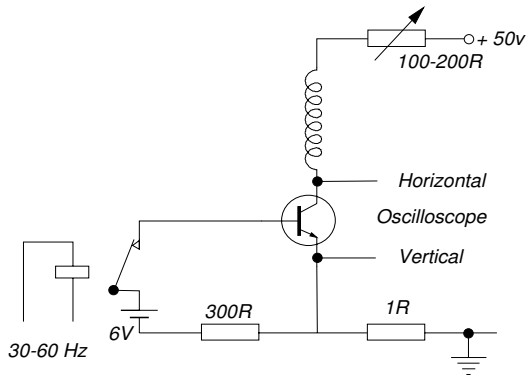


Fig.1. Test circuit for $V_{CEOsust}$.

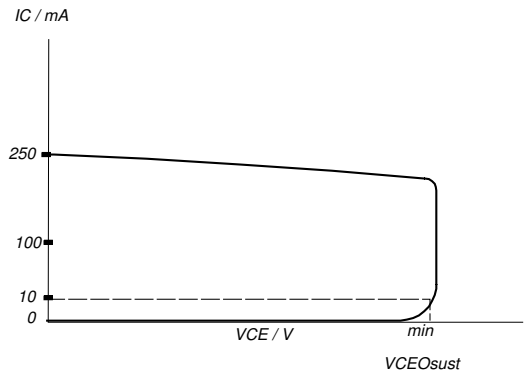


Fig.2. Oscilloscope display for $V_{CEOsust}$.

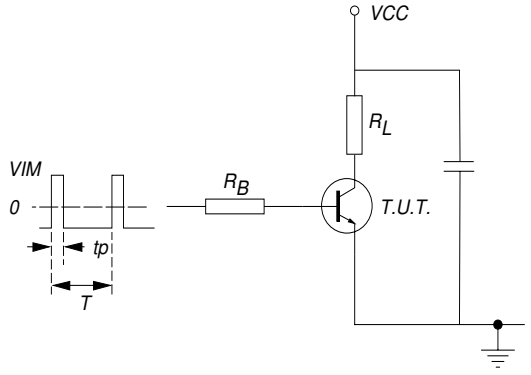


Fig.3. Test circuit resistive load. V_{IM} = -6 to +8 V
V_{CC} = 250 V; t_p = 20 μs; δ = t_p / T = 0.01.
R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

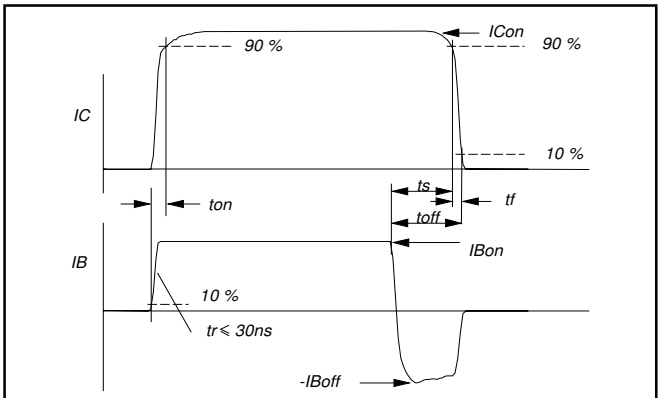


Fig.4. Switching times waveforms with resistive load.

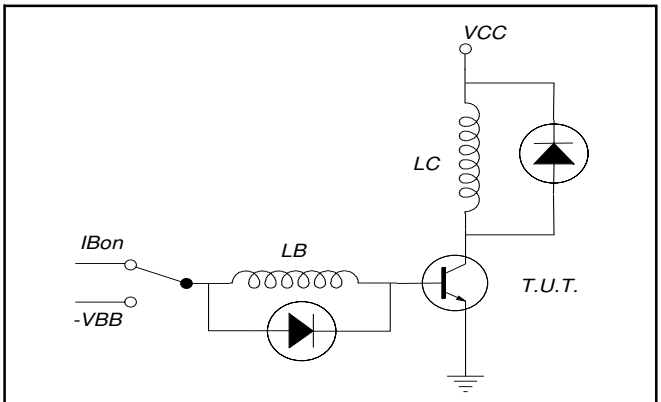


Fig.5. Test circuit inductive load.
V_{CC} = 300 V; -V_{BE} = 5 V; L_C = 200 uH; L_B = 1 uH

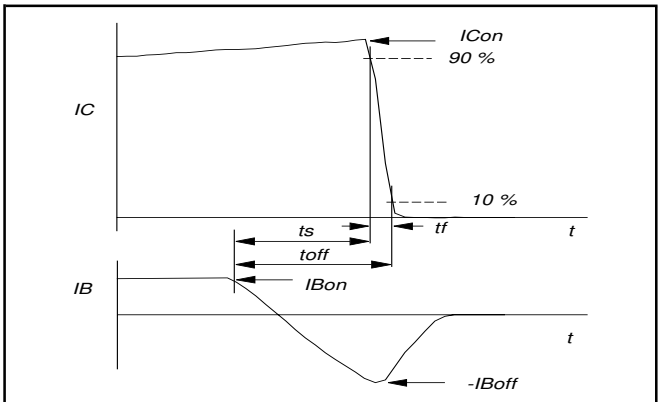


Fig.6. Switching times waveforms with inductive load.

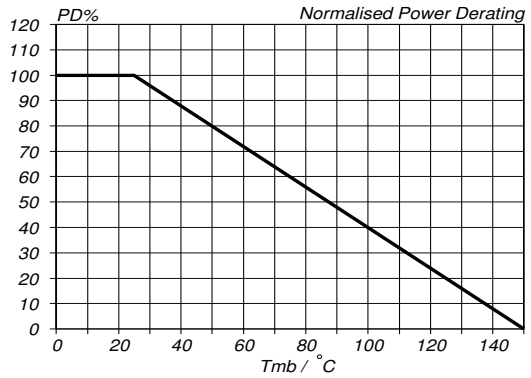


Fig.7. Normalised power dissipation. PD% = 100·PD/PD $_{25°C}$ = f (T_{mb})

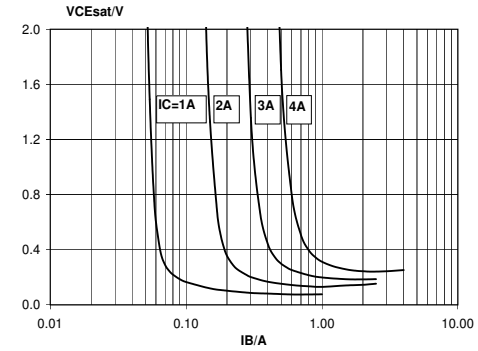


Fig.10. Collector-Emitter saturation voltage. Solid lines = typ values, V_{CEsat} = f(IB); T_j=25˚C.

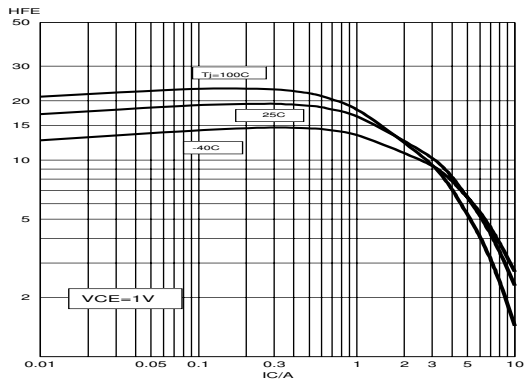


Fig.8. Typical DC current gain. h_{FE} = f(I_C) parameter V_{CE}

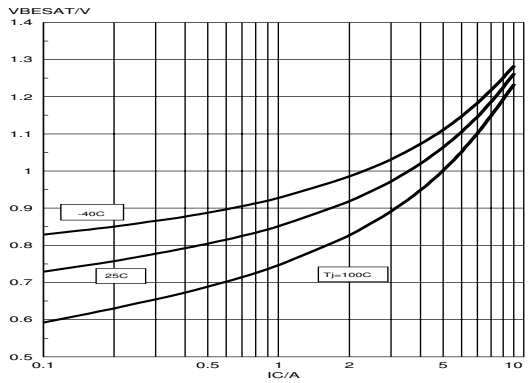


Fig.11. Base-Emitter saturation voltage. Solid lines = typ values, V_{BEsat} = f(IC); at IC/IB =4.

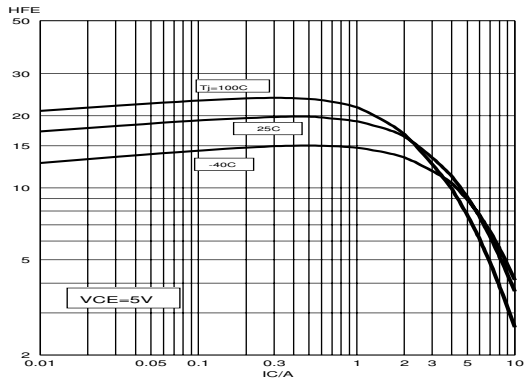


Fig.9. Typical DC current gain. h_{FE} = f(I_C) parameter V_{CE}

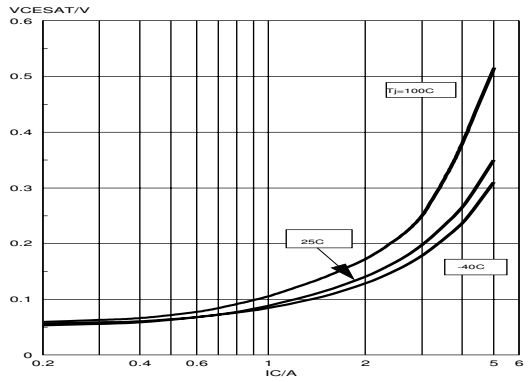


Fig.12. Collector-Emitter saturation voltage. Solid lines = typ values, V_{CEsat} = f(IC); at IC/IB =4.

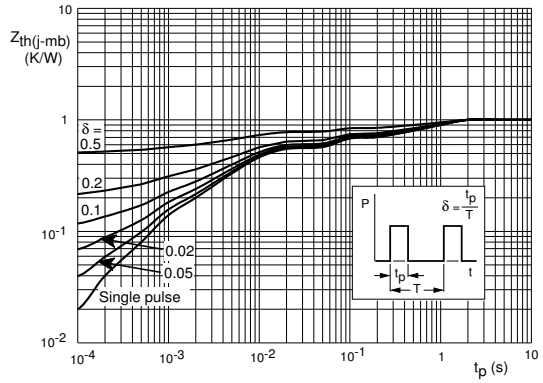


Fig.13. Transient thermal impedance. $Z_{th\ j\text{-}mb} = f(t)$; parameter $\delta = t_p/T$

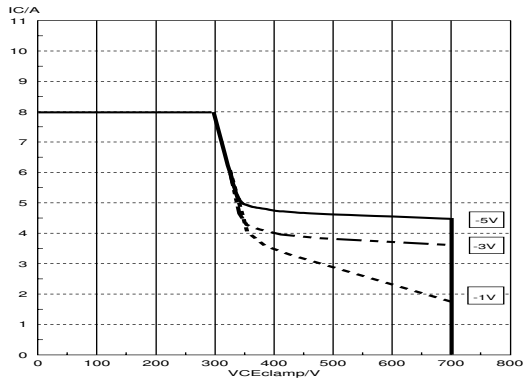


Fig.15. Reverse bias safe operating area ($T_j < T_{jmax}$) for $-V_{BE}$ = 5V,3V & 1V.

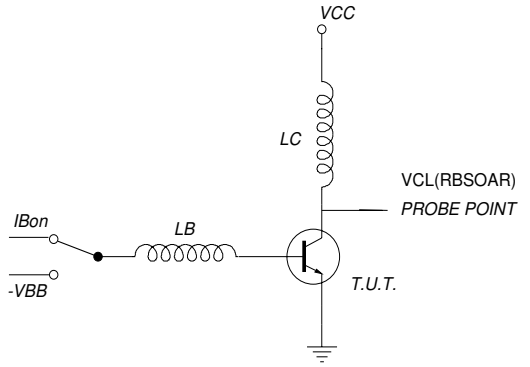
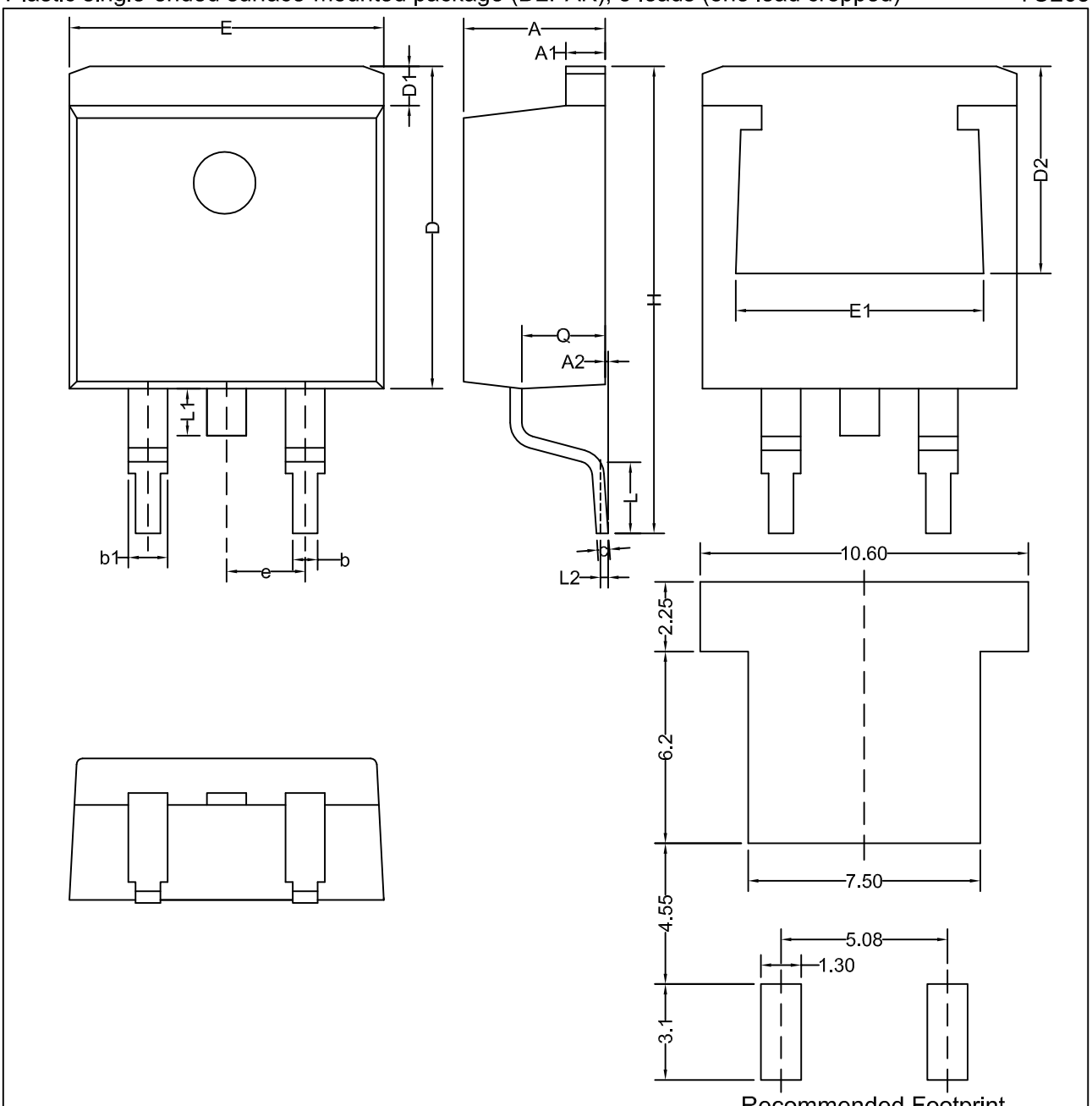


Fig.14. Test circuit for reverse bias safe operating area.

V_{clamp} < 700V; V_{cc} = 150V; $-V_{be}$ = 5V,3V & 1V; L_B = 1μH; L_C = 200μH.

MECHANICAL DATA

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) TO263



	A	A1	A2	b	b1	c	D	D1	D2	e	E	E1	H	L	L1	L2	Q
min	4.10	1.22	0.00	0.60	1.05	0.34	---	1.20	6.60	2.54 (BSC)	9.70	7.80	14.80	2.10	---	0.25 (BSC.)	2.20
max	4.70	1.40	0.25	0.90	1.45	0.64	11.00	1.60	---		10.30	---	15.80	2.90	1.75		2.79

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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